

Six-Pack XPT IGBT

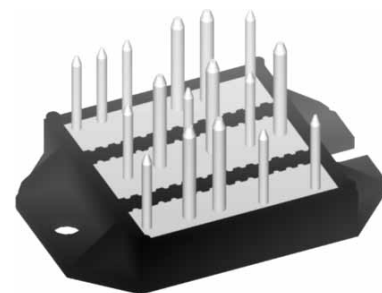
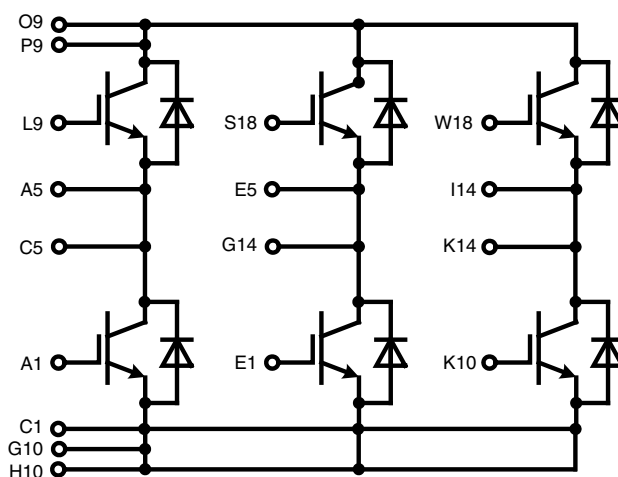
$$V_{CES} = 1200 \text{ V}$$

$$I_{C25} = 28 \text{ A}$$

$$V_{CE(sat)} = 2.1 \text{ V}$$

Part name (Marking on product)

MIXA20W1200MC



Features:

- Easy paralleling due to the positive temperature coefficient of the on-state voltage
- Rugged XPT design (Xtreme light Punch Through) results in:
 - short circuit rated for 10 μ sec.
 - very low gate charge
 - square RBSOA @ 3x I_C
 - low EMI
- Thin wafer technology combined with the XPT design results in a competitive low $V_{CE(sat)}$
- SONIC™ diode
 - fast and soft reverse recovery
 - low operating forward voltage

Application:

- AC motor drives
- Solar inverter
- Medical equipment
- Uninterruptible power supply
- Air-conditioning systems
- Welding equipment
- Switched-mode and resonant-mode power supplies

Package:

- "ECO-PAC2" standard package
- Easy to mount with two screws
- Insulated base plate
- Soldering pins for PCB mounting
- Space and weight savings
- Improved temperature and power cycling capability
- High power density

Output Inverter T1 - T6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{CES}	collector emitter voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
V_{GES}	max. DC gate voltage	continuous			± 20		V
V_{GEM}	max. transient collector gate voltage	transient			± 30		V
I_{C25}	collector current	$T_C = 25^{\circ}\text{C}$			28		A
I_{C80}		$T_C = 80^{\circ}\text{C}$			20		A
P_{tot}	total power dissipation	$T_C = 25^{\circ}\text{C}$			100		W
$V_{CE(sat)}$	collector emitter saturation voltage	$I_C = 16\text{ A}; V_{GE} = 15\text{ V}$		1.8 2.1	2.1		V V
$V_{GE(th)}$	gate emitter threshold voltage	$I_C = 0.6\text{ mA}; V_{GE} = V_{CE}$	5.5	6.0	6.5		V
I_{CES}	collector emitter leakage current	$V_{CE} = V_{CES}; V_{GE} = 0\text{ V}$		0.02 0.2	0.2		mA mA
I_{GES}	gate emitter leakage current	$V_{GE} = \pm 20\text{ V}$			500		nA
$Q_{G(on)}$	total gate charge	$V_{CE} = 600\text{ V}; V_{GE} = 15\text{ V}; I_C = 15\text{ A}$		47			nC
$t_{d(on)}$	turn-on delay time	inductive load $V_{CE} = 600\text{ V}; I_C = 15\text{ A}$ $V_{GE} = \pm 15\text{ V}; R_G = 56\ \Omega$	$T_{VJ} = 125^{\circ}\text{C}$	70			ns
t_r	current rise time			40			ns
$t_{d(off)}$	turn-off delay time			250			ns
t_f	current fall time			100			ns
E_{on}	turn-on energy per pulse			1.55			mJ
E_{off}	turn-off energy per pulse			1.7			mJ
RBSOA	reverse bias safe operating area	$V_{GE} = \pm 15\text{ V}; R_G = 56\ \Omega;$	$T_{VJ} = 125^{\circ}\text{C}$ $V_{CEK} = 1200\text{ V}$		45		A
SCSOA	short circuit safe operating area	$V_{CE} = 900\text{ V}; V_{GE} = \pm 15\text{ V};$	$T_{VJ} = 125^{\circ}\text{C}$		10		μs
t_{SC}	short circuit duration	$R_G = 56\ \Omega;$ non-repetitive		60			A
I_{SC}	short circuit current						
R_{thJC}	thermal resistance junction to case	(per IGBT)			1.3		K/W

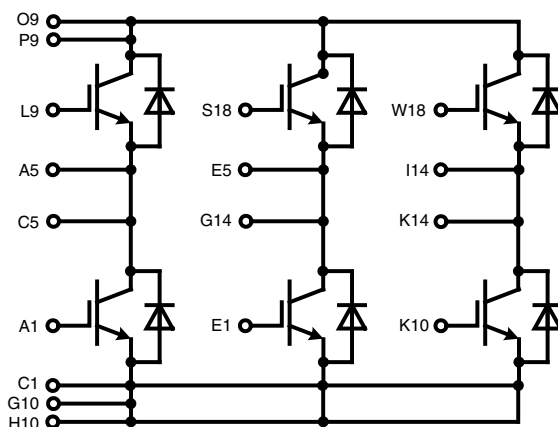
Output Inverter D1 - D6

Symbol	Definitions	Conditions	min.	Ratings			Unit
				typ.	max.		
V_{RRM}	max. repetitive reverse voltage	$T_{VJ} = 25^{\circ}\text{C}$			1200		V
I_{F25}	forward current	$T_C = 25^{\circ}\text{C}$			33		A
I_{F80}		$T_C = 80^{\circ}\text{C}$			22		A
V_F	forward voltage	$I_F = 20\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 25^{\circ}\text{C}$ $T_{VJ} = 150^{\circ}\text{C}$	1.95 1.85	2.2		V V
Q_{rr}	reverse recovery charge	$V_R = 600\text{ V}$ $di_F/dt = -400\text{ A}/\mu\text{s}$ $I_F = 20\text{ A}; V_{GE} = 0\text{ V}$	$T_{VJ} = 125^{\circ}\text{C}$	3			μC
I_{RM}	max. reverse recovery current			20			A
t_{rr}	reverse recovery time			350			ns
E_{rec}	reverse recovery energy			0.7			mJ
R_{thJC}	thermal resistance junction to case	(per diode)			1.5		K/W

 $T_C = 25^{\circ}\text{C}$ unless otherwise stated

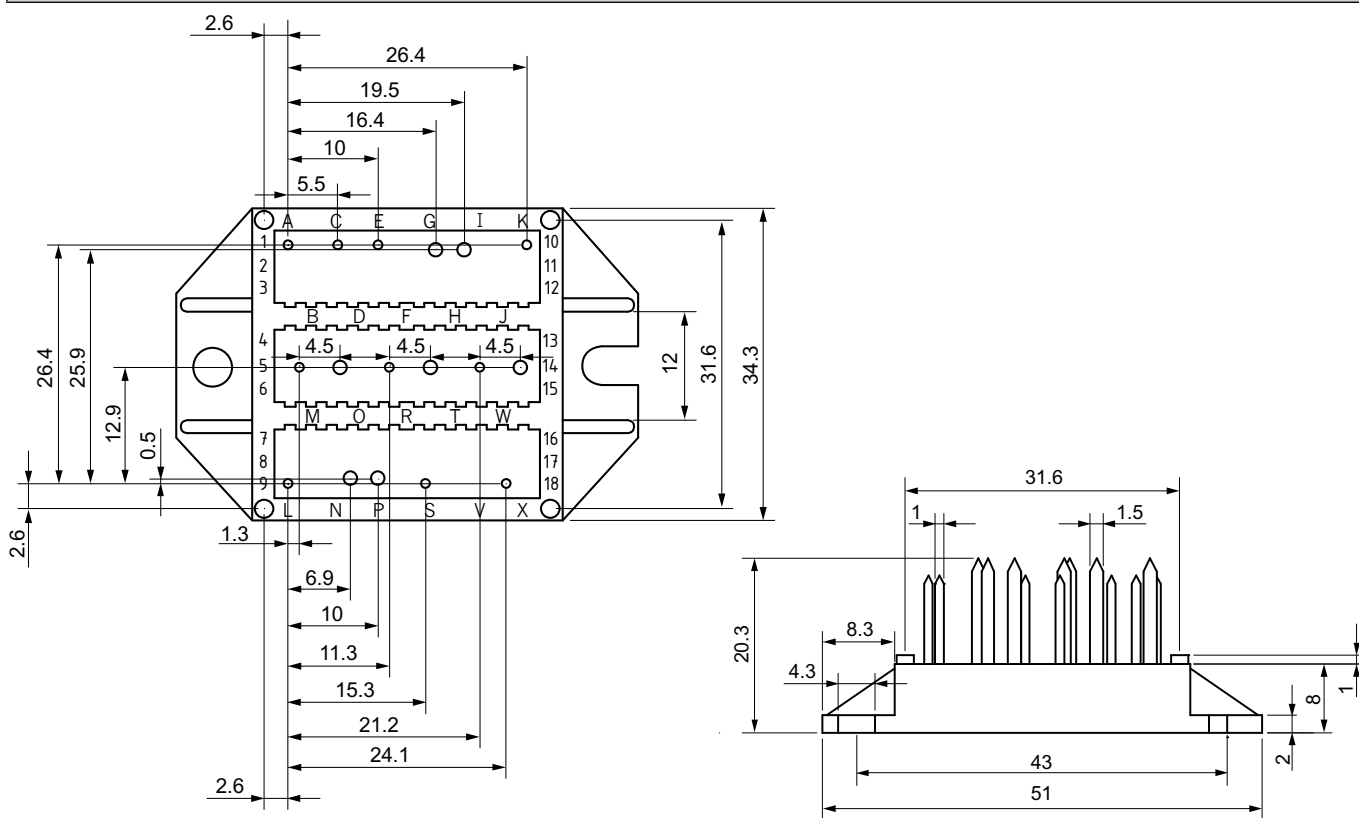
Module						
Symbol	Definitions	Conditions	Ratings			Unit
			min.	typ.	max.	
T_{VJ}	operating temperature		-40		125	°C
T_{VJM}	max. virtual junction temperature				150	°C
T_{stg}	storage temperature		-40		125	°C
V_{ISOL}	isolation voltage	$I_{ISOL} \leq 1 \text{ mA}; 50/60 \text{ Hz}; t = 1 \text{ s}$			3600	V~
M_d	mounting torque (M5)		1.5		2	Nm
d_s	creep distance on surface		11.2			mm
d_A	strike distance through air		11.2			mm
Weight				24		g

Circuit Diagram

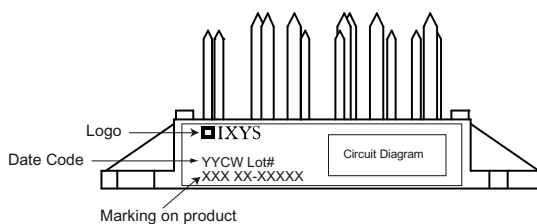


Outline Drawing

Dimensions in mm (1 mm = 0.0394")



Product Marking



Part number

M = Module
I = IGBT
X = XPT
A = Standard
20 = Current Rating [A]
W = Six-Pack
1200 = Reverse Voltage [V]
MC = ECO-PAC2

Ordering	Part Name	Marking on Product	Delivering Mode	Base Qty	Ordering Code
Standard	MIXA20W1200MC	MIXA20W1200MC	Box	6	509537

IXYS reserves the right to change limits, test conditions and dimensions.

20110304b

Inverter T1 - T6

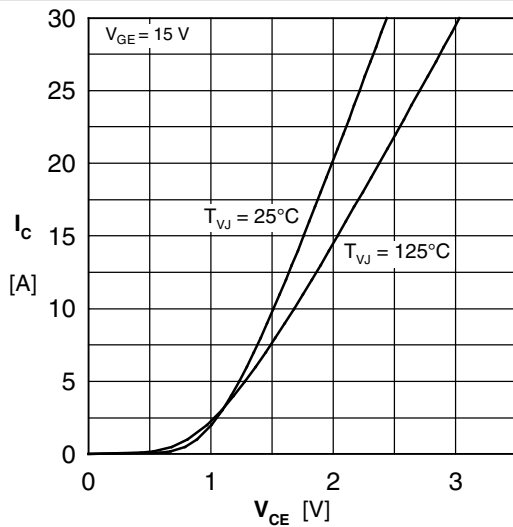


Fig. 1 Typ. output characteristics

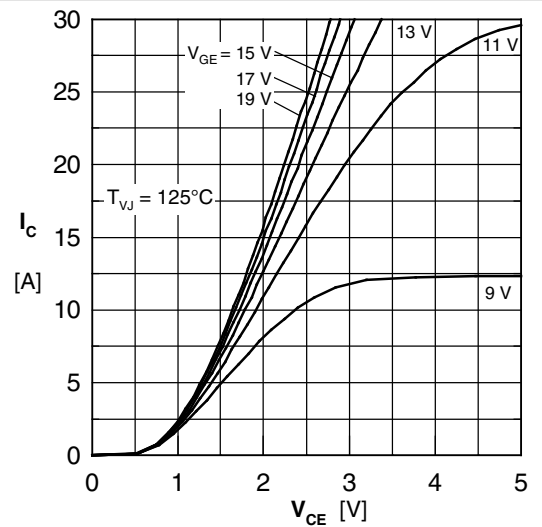


Fig. 2 Typ. output characteristics

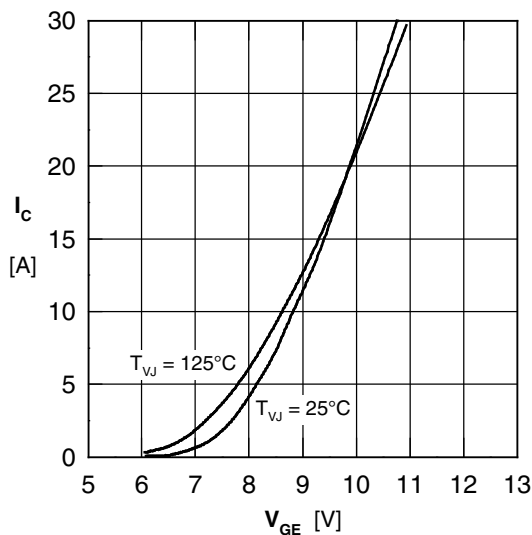


Fig. 3 Typ. transfer characteristics

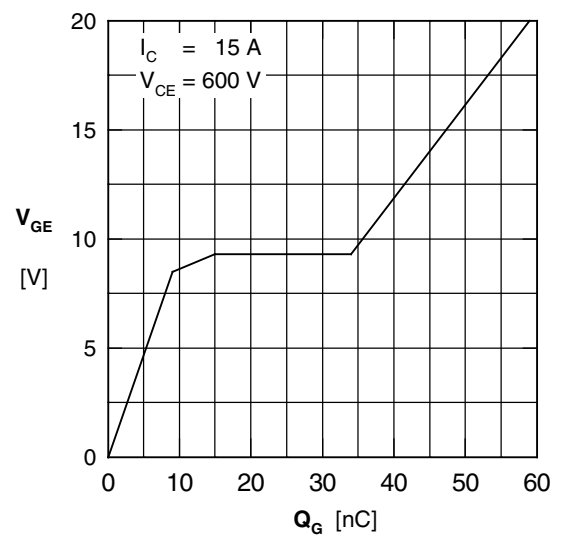


Fig. 4 Typ. turn-on gate charge

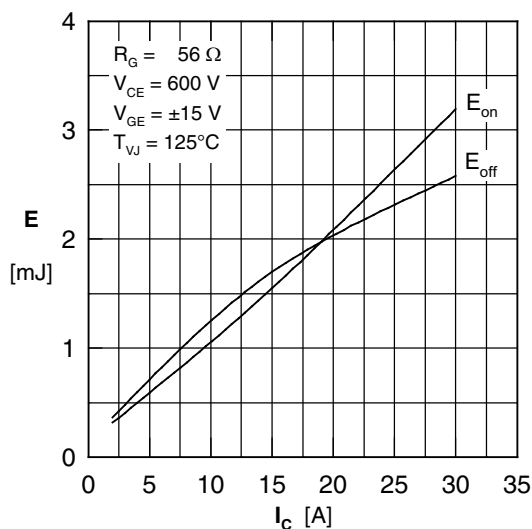


Fig. 5 Typ. switching energy vs. collector current

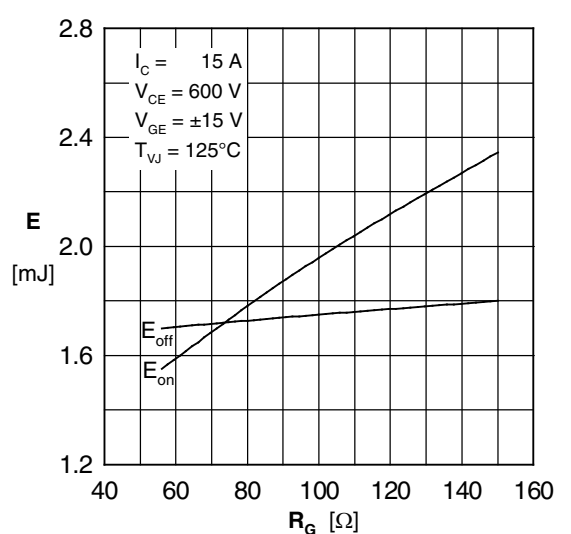


Fig. 6 Typ. switching energy vs. gate resistance

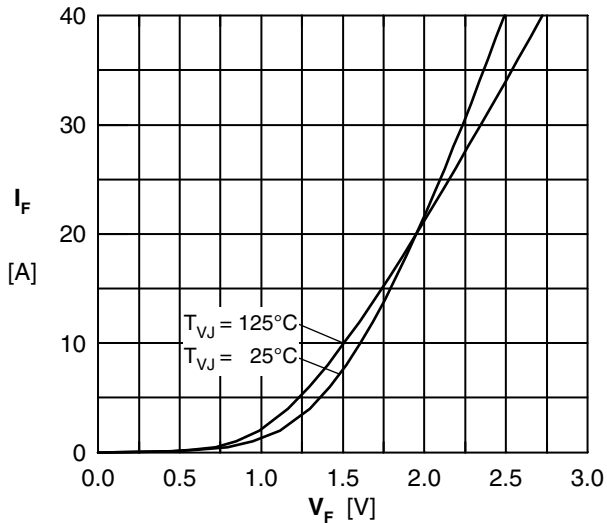


Fig. 7 Typ. Forward current versus V_F

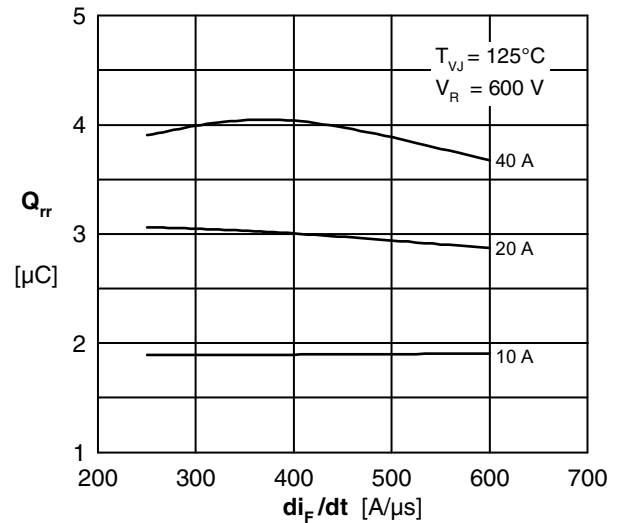


Fig. 8 Typ. reverse recov.charge Q_{rr} vs. di/dt

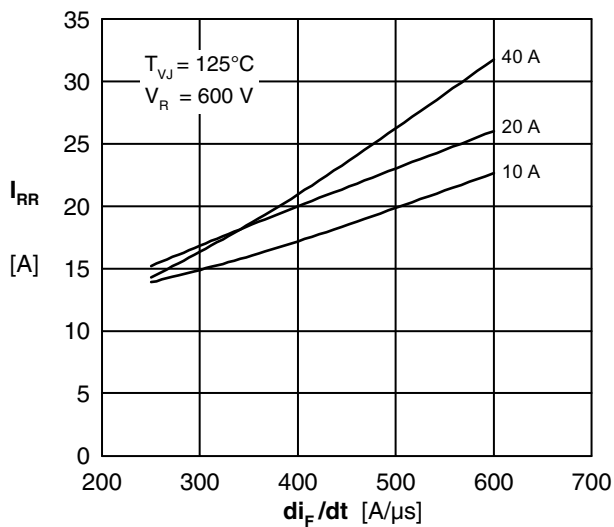


Fig. 9 Typ. peak reverse current I_{RM} vs. di/dt

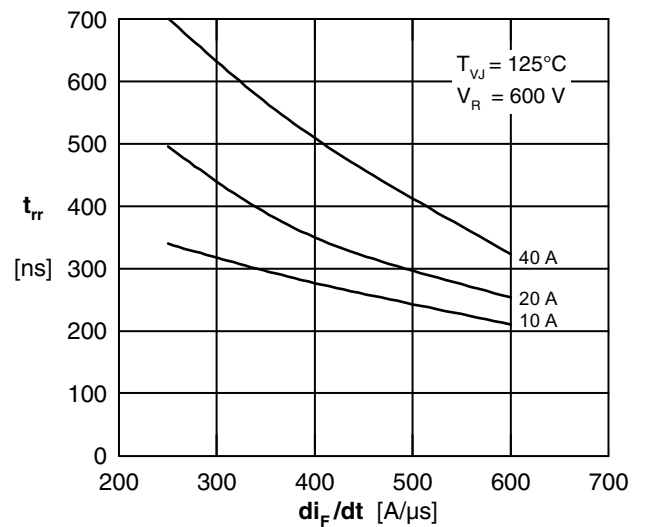


Fig. 10 Typ. recovery time t_{rr} versus di/dt

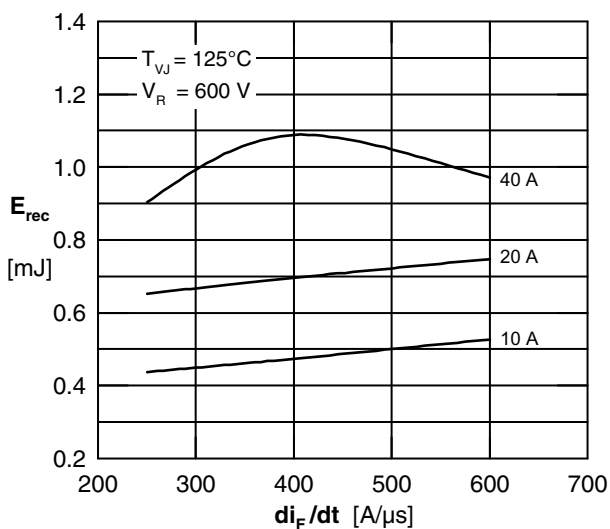


Fig. 11 Typ. recovery energy E_{rec} versus di/dt

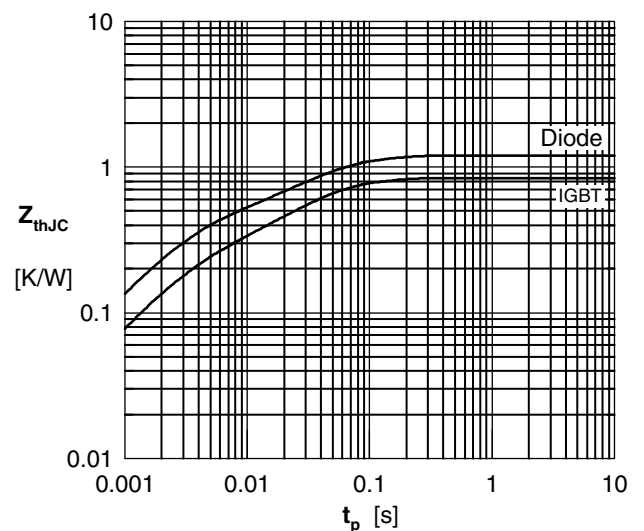


Fig. 12 Typ. transient thermal impedance